
Tests for preparing the GaAs test beam at DESY

Sandro Kollowa

BTU Cottbus / DESY Zeuthen

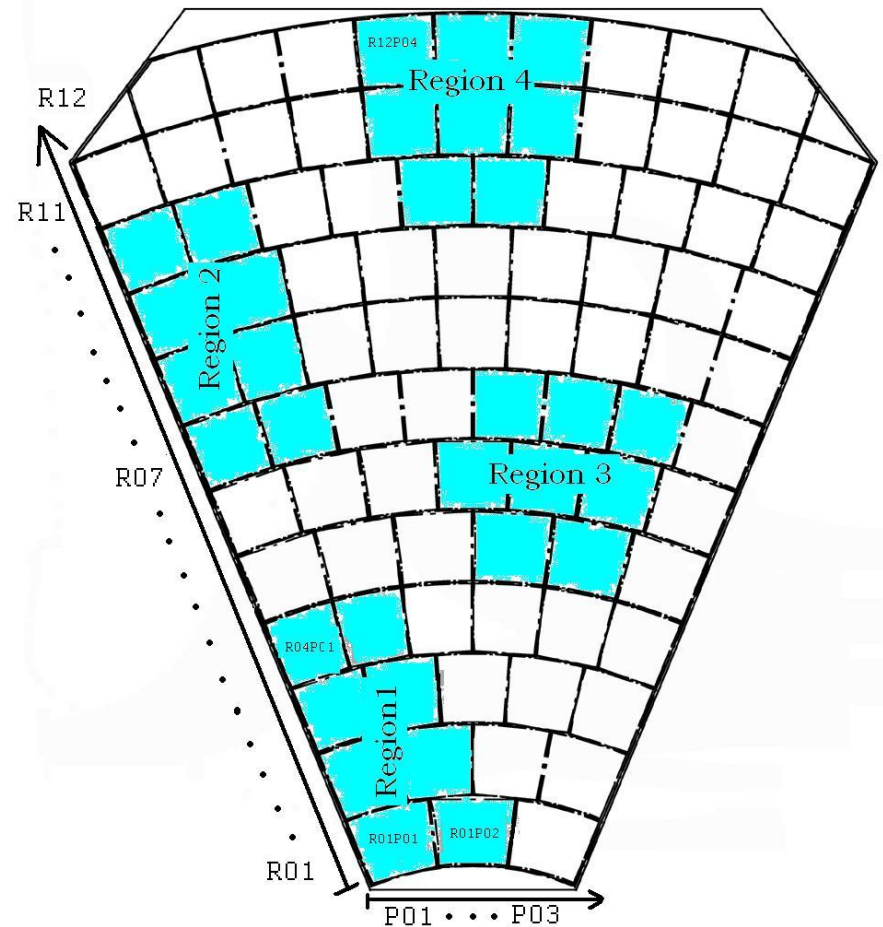
Outline

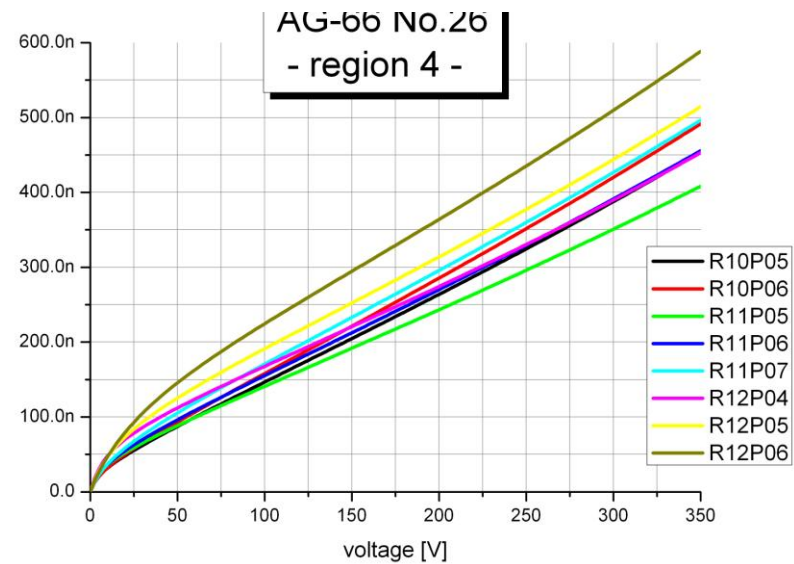
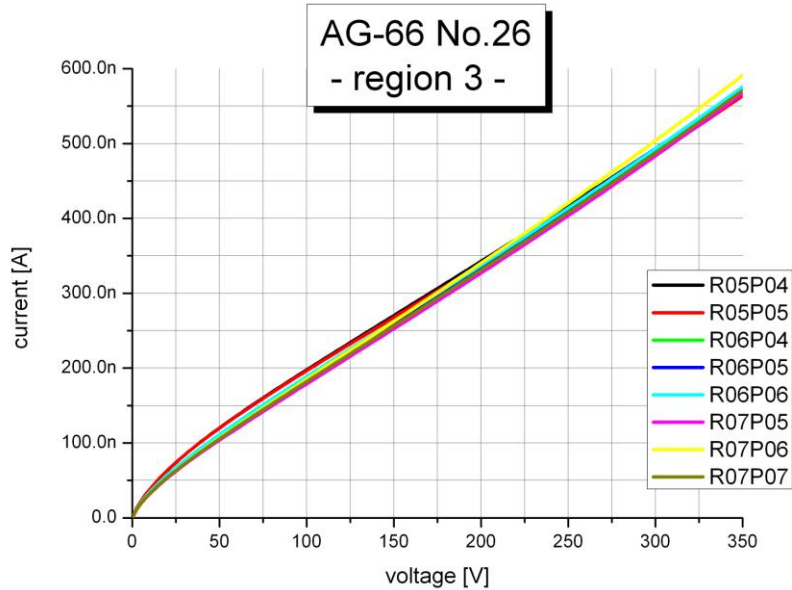
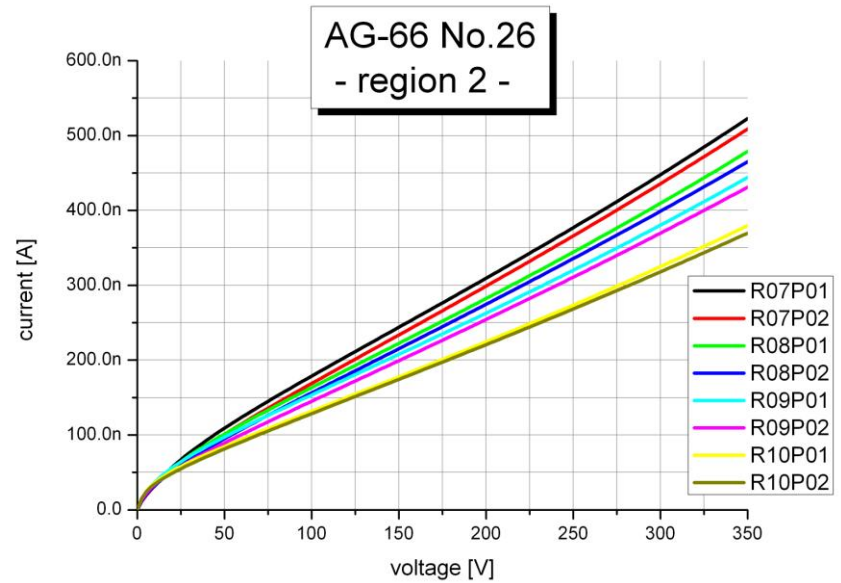
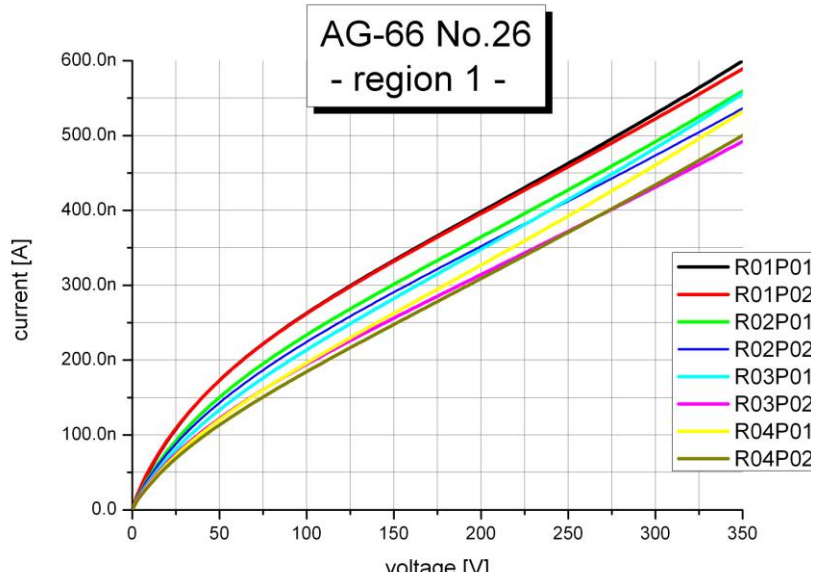
- GaAs detectors
 - IV-measurements
- Fanout
 - Capacitance measurements
- Readout chips
 - linearity test
 - signal size
 - signal to noise
 - calibration



GaAs-sensors: IV-measurements

- was planned to irradiate 32 pads in 4 clusters in the test beam
- have five GaAs-sensor prototypes (AG-66/7; AG-66/21; AG-66/26; AG-66/34 and AG-84/5)
- measured IV-curves for all 32 pads for each sensor
- applied voltages:
 - 0V ... 350V
 - 2.5V-steps

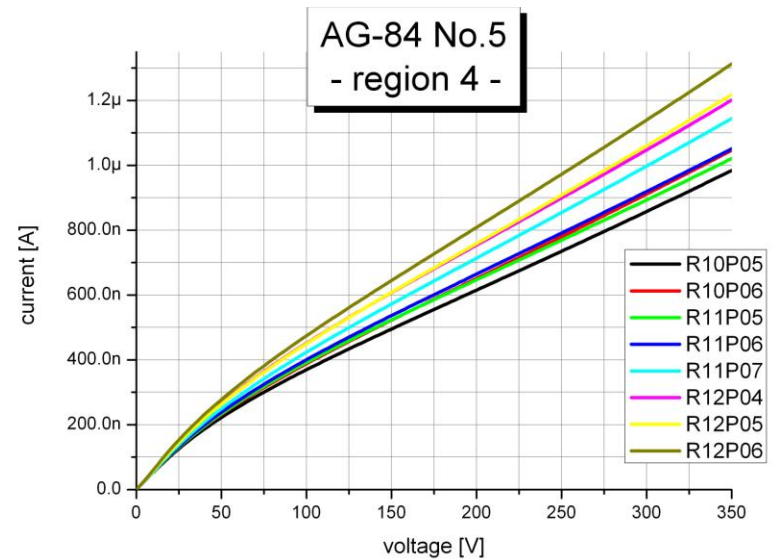
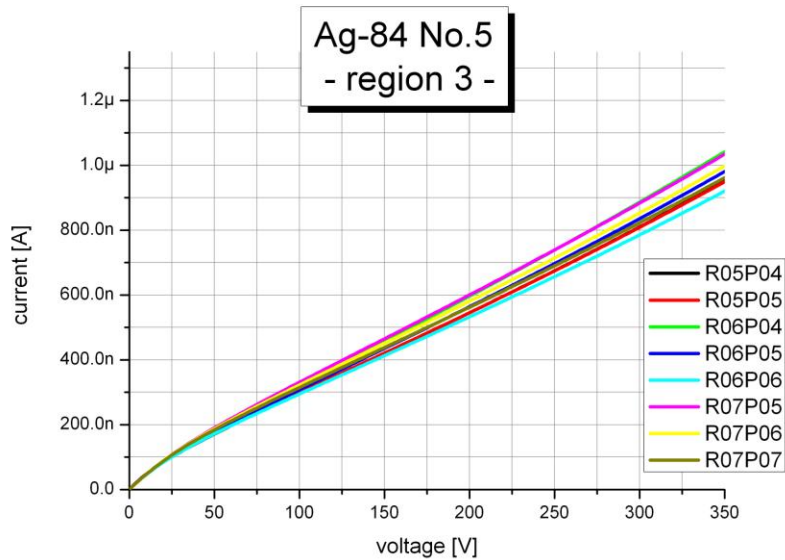
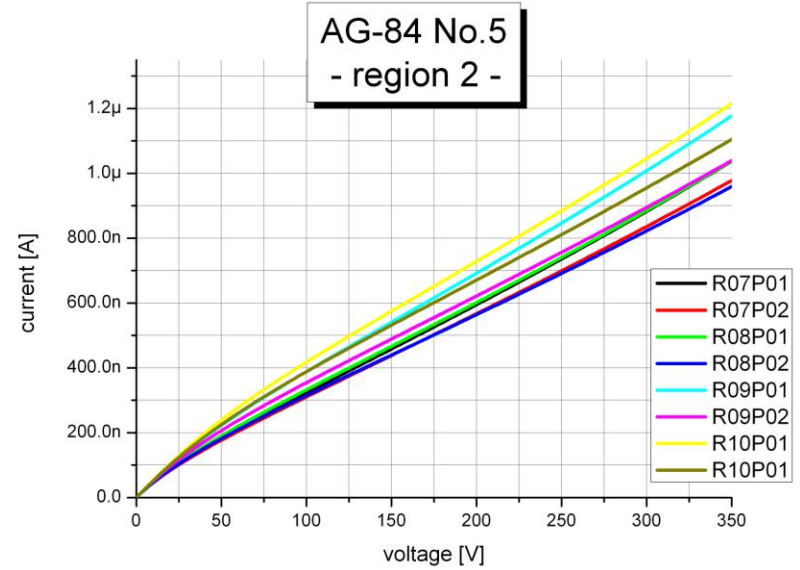
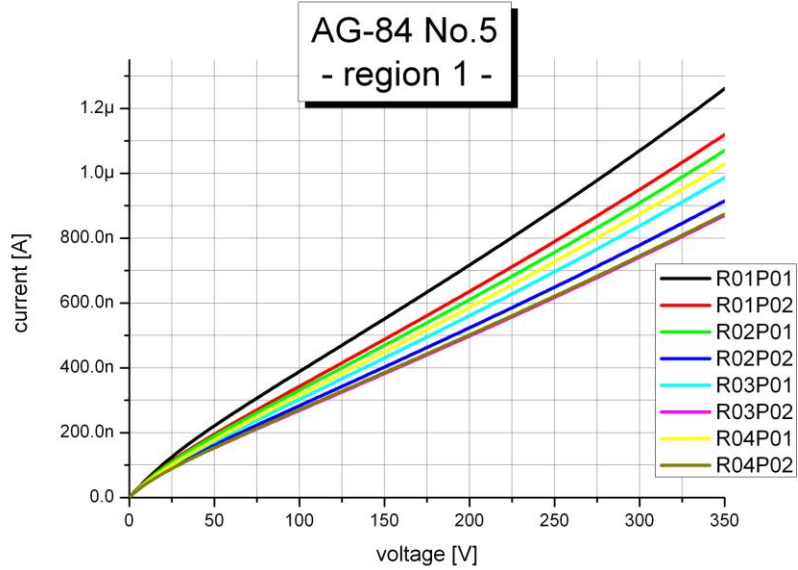




stats @ 350V:

min: 370 nA
max: 600 nA

average: 513 nA
variation: 38.4%



stats @ 350V:

min: 870 nA
max: 1.31 μA

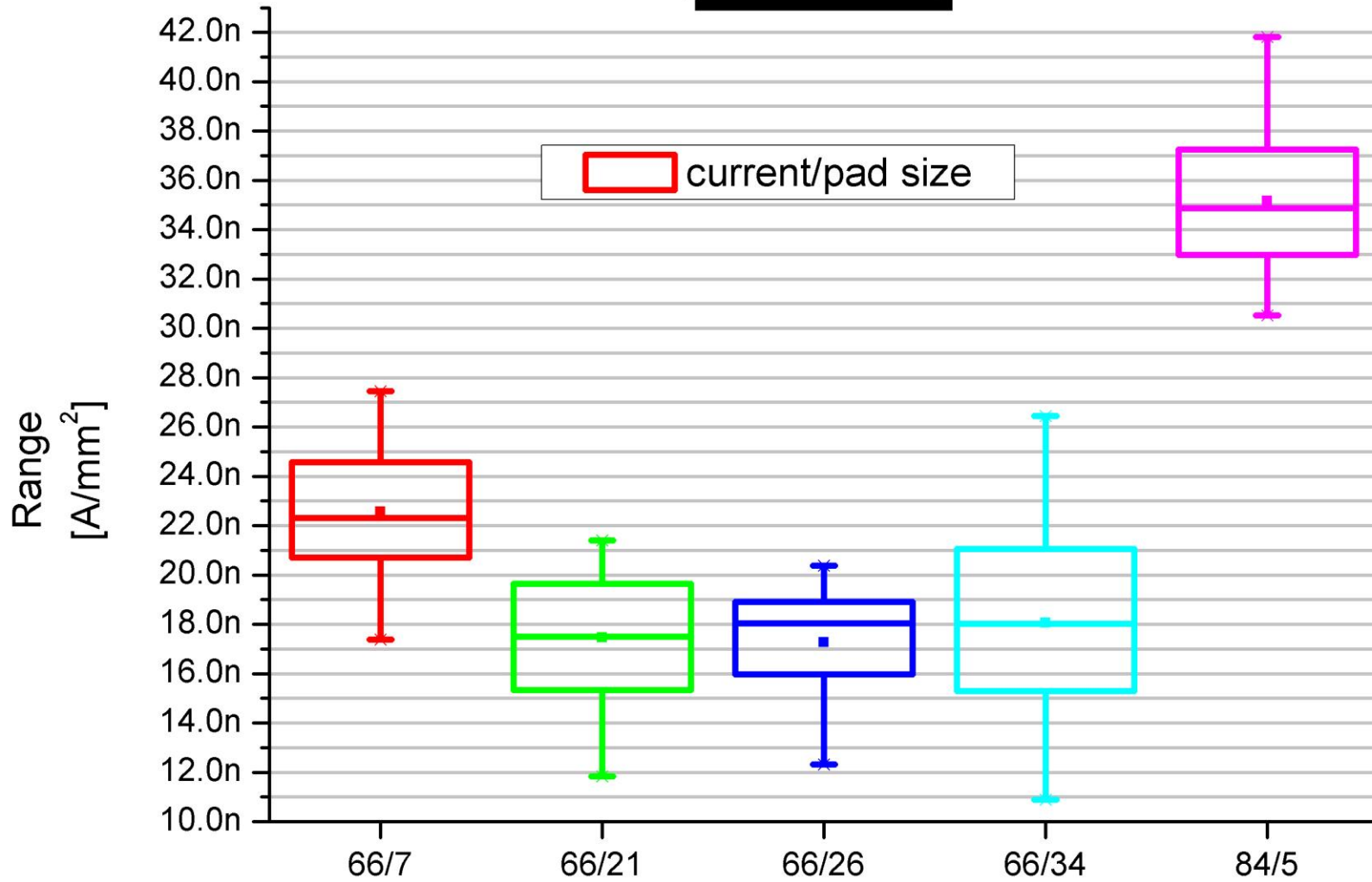
average: 1.05 μA
variation: 33.7%

Comparison of the sensors

- pad sizes differs in a range of 15%
- for comparison the current at 350V was divided by pad size

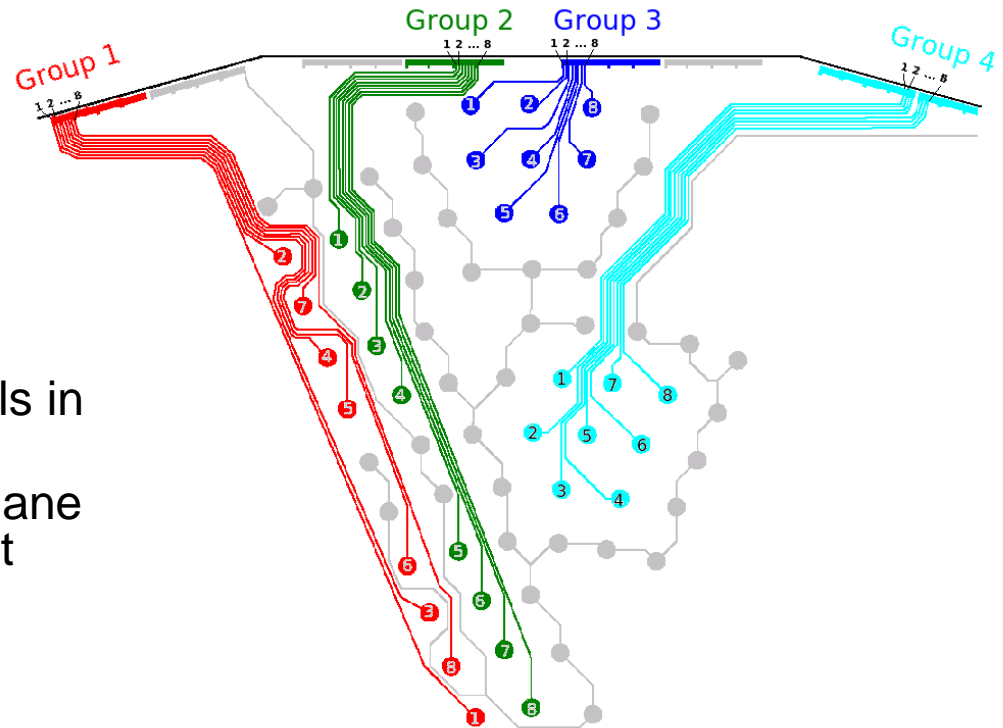
current per pad size		
sensor	arithmetic mean	standard deviation
	[nA/mm ²]	[nA/mm ²]
66/7	22.57	2.63
66/21	17.47	2.53
66/26	17.26	2.19
66/34	18.05	4.05
84/5	35.15	3.02

Boxplots



Fanout: capacitances

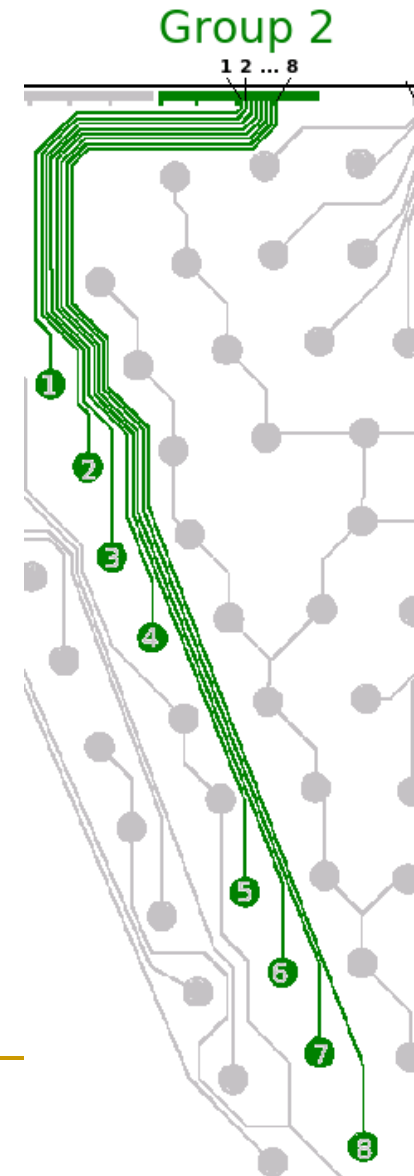
- Measurement device:
 - C-Meter (Hewlett Packard 4263B LCR Meter)
 - used settings:
 - 1000 mV amplitude
 - 100 kHz frequency
- Measurements for group 2:
 - capacitance between one channel and all other channels in parallel
 - one channel vs. all + metal plane on the backside of the Fanout
 - metal plane simulates the metalized surface of the sensor



Fanout: capacitances

Group 2			
channels	capacitance [pF]	channels	capacitance [pF]
5 vs all	3.53	5 vs all+BP	4.47
6 vs all	3.98	6 vs all+BP	4.95
7 vs all	4.32	7 vs all+BP	5.26
8 vs all	2.90	8 vs all+BP	4.68

- largest measured capacitance was 5.26 pF for “channel 7 vs all+BP”



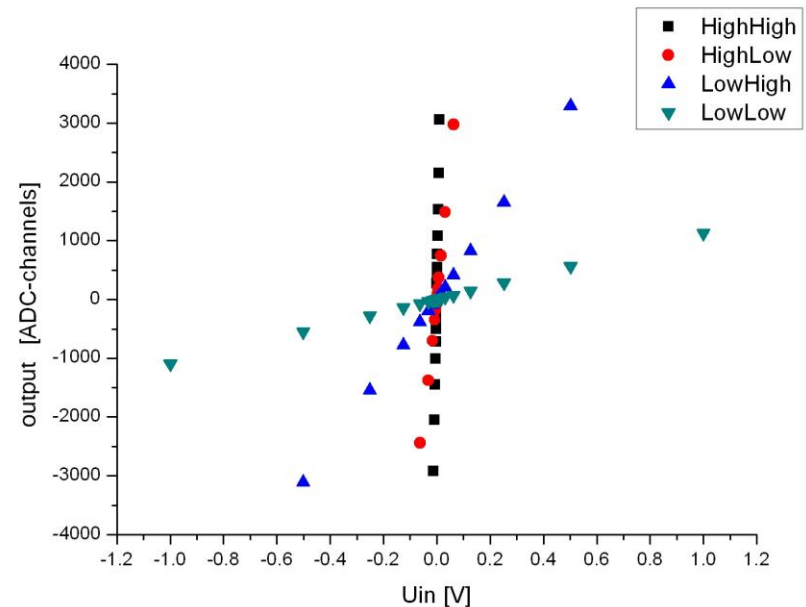
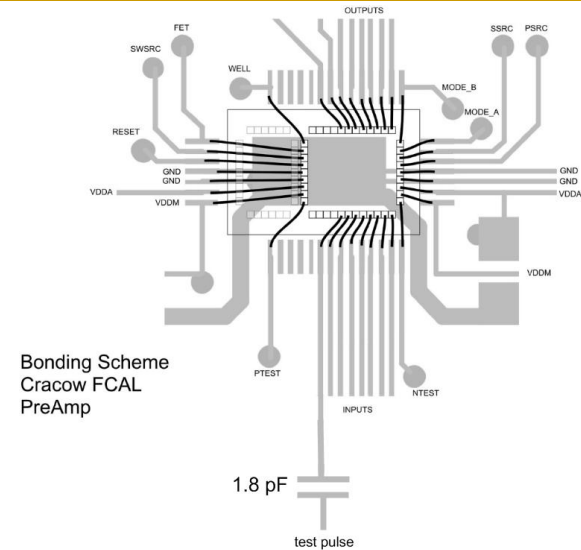
BP = Back Plain (metal plain on the backside of the Fanout)

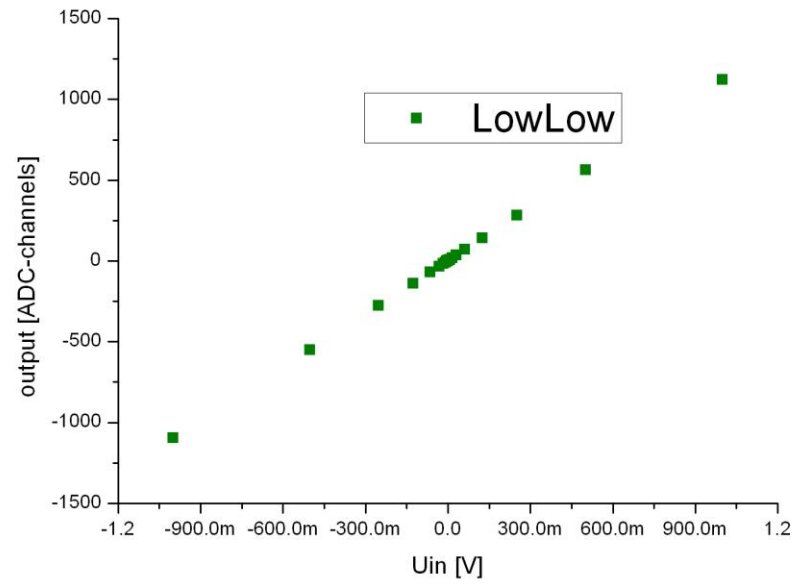
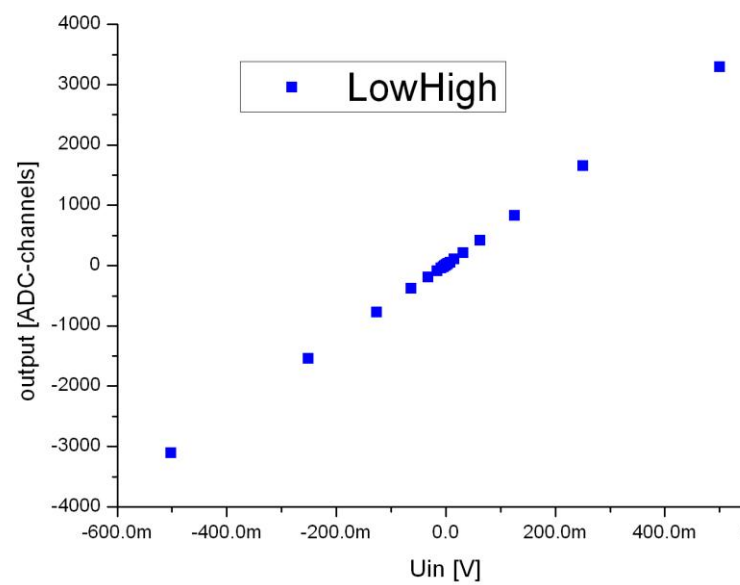
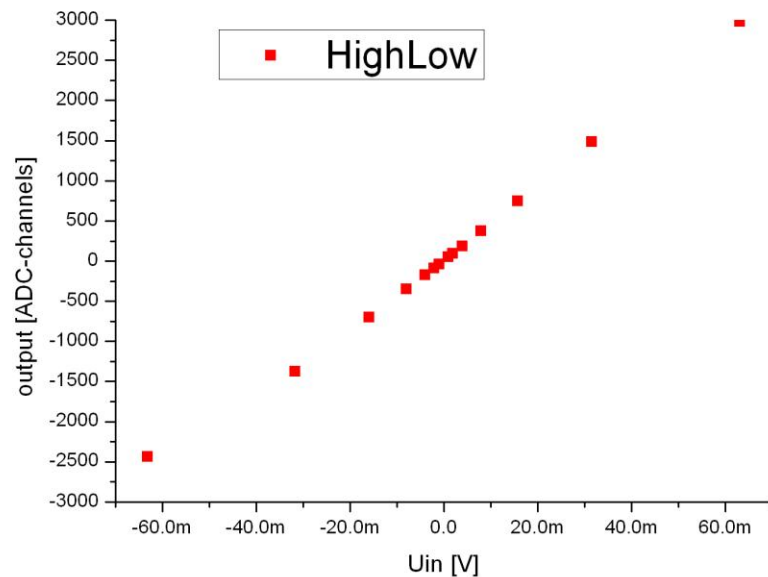
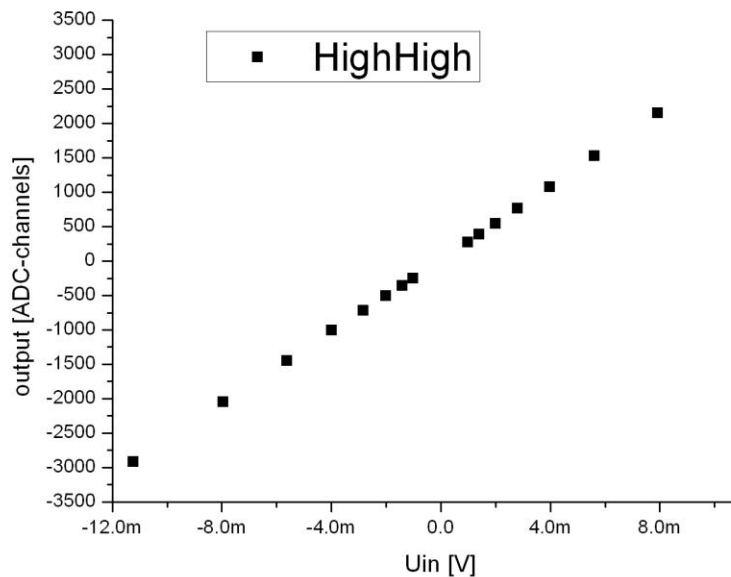
tests on the readout chips

- chips have four possible gain settings
 - preamplifier: High or Low
 - shaper: High or Low
 - chip 1, chip 3, chip 5 were bonded so far
 - Linearity test:
 - for channel 0, chip 1
 - for all four gain settings (HighHigh, HighLow, LowHigh, LowLow)
 - calibration measurements:
 - signal size at fixed input voltage
 - signal to noise
 - done for all channels, all chips and three gain settings (HighHigh, HighLow, LowHigh)
 - DAQ:
 - 8 channel charge integrating ADC (C.A.E.N. V265)
-

Linearity test

- sent test pulses from a pulse generator to channel 0, chip 1
- bonded a capacitor (1.8 pF) directly to chip input
- so we know the input charge from input voltage
- +/-1V pulses by generator
- used attenuator to vary input voltage
 - from 0 dB in 3dB- or 6dB-steps
 - 110dB for pedestal measurements
- converter between board output and ADC input for positiv test pulses (ADC needs negativ input)

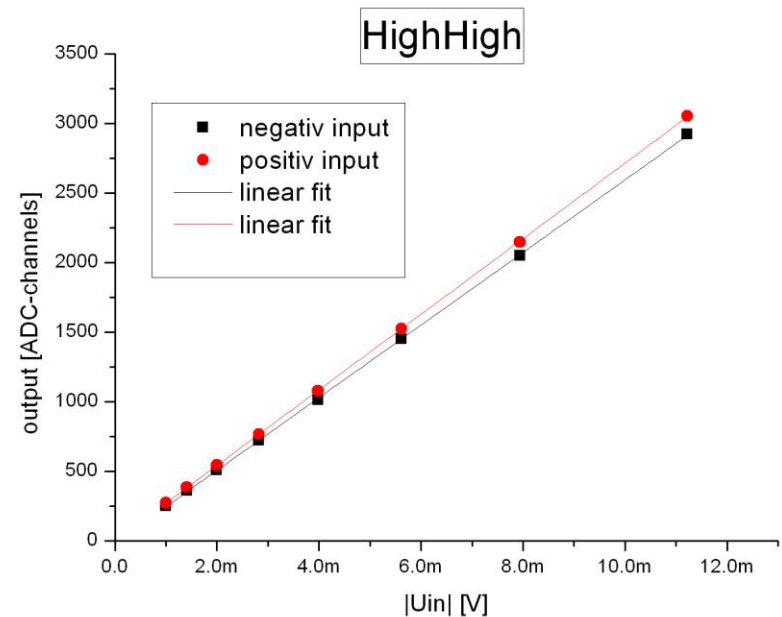




Calibration factors

- separately linear fits for positive and negative input voltage

	Negative U_{in}	Positiv U_{in}
	[ADC-ch./V]	[ADC-ch./V]
HighHigh	261 057	271 703
HighLow	(43 709)*	47 183
LowHigh	6 205	6 572
LowLow	1 098	1 122



*without the value at -63 mV

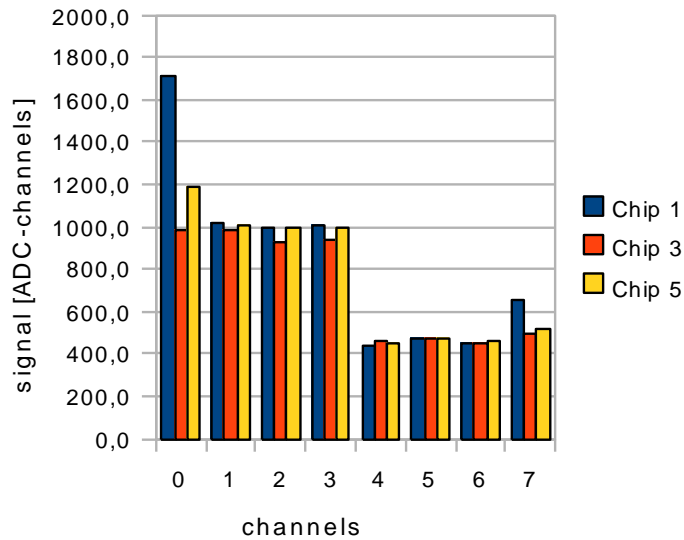
Calibration measurements

- in principle the same setting as before
- external capacitor was removed
- test pulses now send to board input
 - two inputs: one for even and one for odd channels
 - input pulse to 4 channels at the same time
- fixed negative input voltage (42dB = -7.9mV)
- measured all channels, all channels, three gain settings

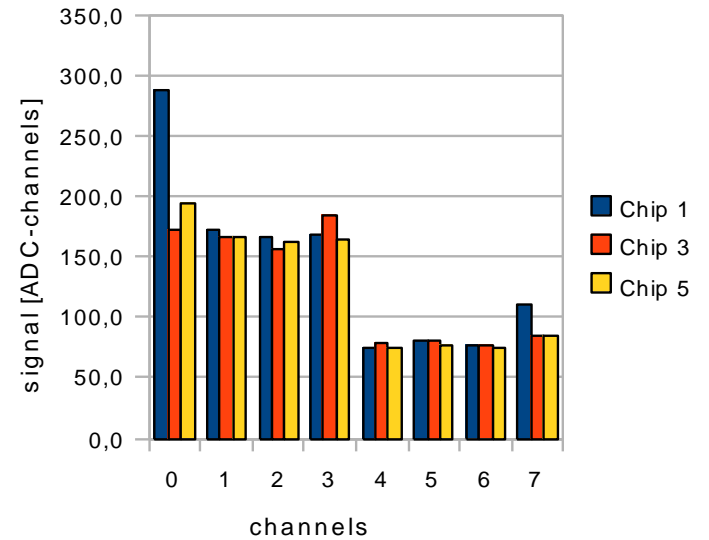


Signal size

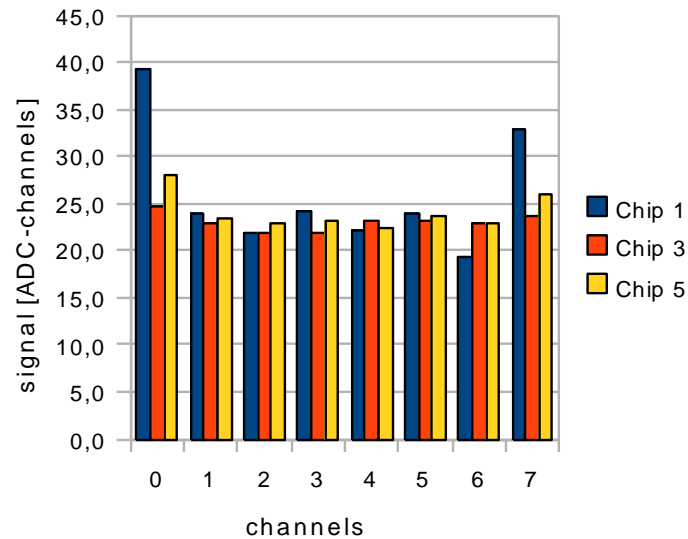
HighHigh



HighLow

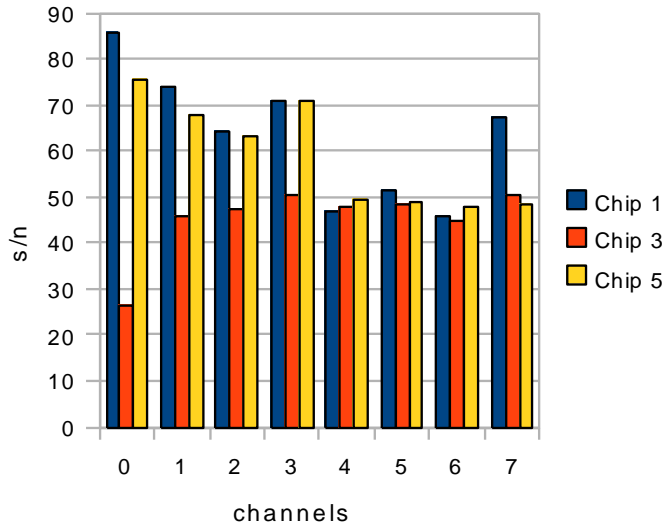


LowHigh

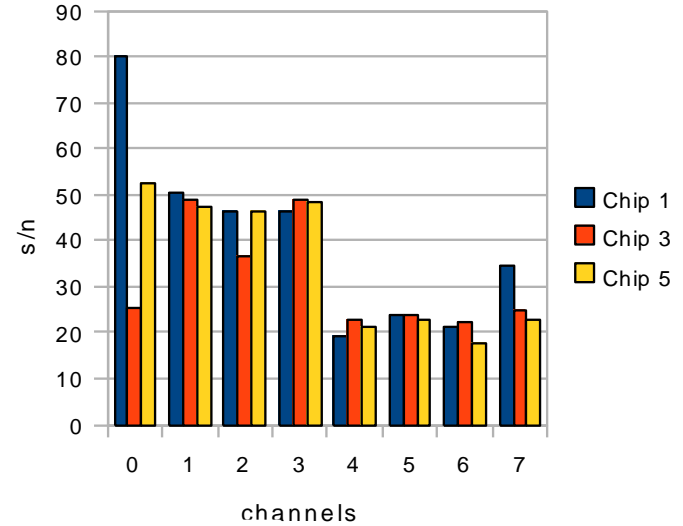


Signal to noise

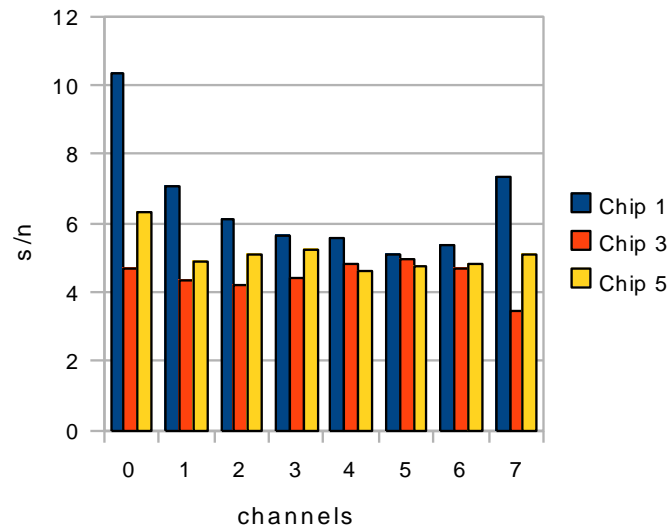
HighHigh



HighLow



LowHigh



Calibration measurements

- idea was to have full calibration with:
 - linearity test on one channel for all gains
 - calibration factors for this channel
 - expect also linearity in all other channels
 - one signal size measurement at fixed input voltage for all channels in all chips
 - but channel 0 in chip 1 showed much higher signals
 - also different S/N-values for chip 3
 - better to have linearity tests for all channels
-

Summery

- different measurements for test beam preparation were done
 - IV-measurements for sensors:
 - comparison of the 5 sensors -> choice for test beam
 - check if pads are damaged
 - know dark current for each pad
 - Capacitance measurement for Fanout
 - for cross talk estimation
 - Tests for readout chips
 - linearity test and calibration measurement for one channel
 - comparison of signal size and signal to noise for all channels, all chips
 - estimation for calibration for all channels
-

Thank you
